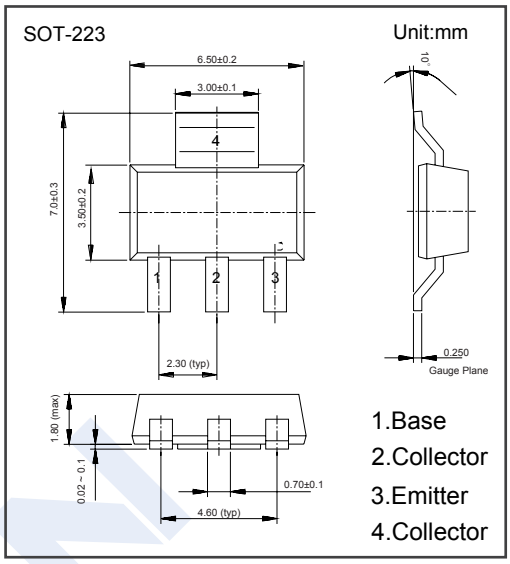
NPN Transistors

PZT3904 (KZT3904)



■ Features

- Low Voltage and Low Current
- General Purpose Amplifier and Switch Application
- Complementary to PZT3906

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	60	V
Collector - Emitter Voltage	V_{CEO}	40	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	200	mA
Collector Power Dissipation	P_C	1	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	125	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 μA， I_E= 0	60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA， I_B= 0	40			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 μ A， I_C= 0	6			
Collector-base cut-off current	I_{CBO}	V_{CB}= 60 V , I_E= 0			100	nA
Collector cut-off current	I_{CEX}	V_{CE}= 30 V , $V_{EB(off)}$=-3V			50	
Emitter cut-off current	I_{EBO}	V_{EB}= 6V , I_C=0			100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10 mA, I_B=1mA			0.2	V
		I_C= 50 mA, I_B= 5mA			0.3	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=10 mA, I_B=1mA	0.65		0.85	
		I_C= 50 mA, I_B= 5mA			0.95	
DC current gain	$h_{FE(1)}$	V_{CE}= 1V, I_C= 0.1mA	40			
	$h_{FE(2)}$	V_{CE}= 1V, I_C= 1mA	70			
	$h_{FE(3)}$	V_{CE}= 1V, I_C= 10mA	100		300	
	$h_{FE(4)}$	V_{CE}= 1V, I_C= 50mA	60			
Delay time	t_d	V_{CC}=3V, $V_{BE(off)}$=-0.5V I_C=10mA, I_{B1}=-I_{B2}=1mA			35	nS
Rise time	t_r				35	
Storage time	t_s	V_{CC}=3V, I_C=10mA, I_{B1}=-I_{B2}=1mA			200	
Fall time	t_f				50	
Collector output capacitance	C_{ob}	V_{CB}= 5V, I_E= 0,f=1MHz			4	pF
Transition frequency	f_T	V_{CE}= 20V, I_C= 10mA,f=100MHz	300			MHz